

# isc N-Channel Mosfet Transistor

# STF19NM50N

#### • FEATURES

- Drain Current I<sub>D</sub>= 14A@ T<sub>C</sub>=25℃
- Drain Source Voltage-
  - : V<sub>DSS</sub>= 500V(Min)
- · Fast Switching Speed
- · 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

#### APPLICATIONS

· Switching applications

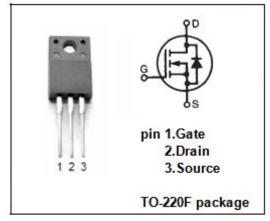


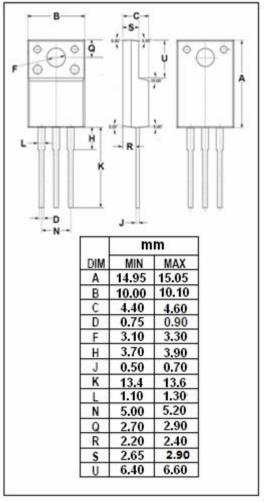
## • ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

| SYMBOL           | PARAMETER                                     | VALUE        | UNIT         |
|------------------|---|--------------|--------------|
| V <sub>DSS</sub> | Drain-Source Voltage                          | 500          | V            |
| $V_{GS}$         | Gate-Source Voltage                           | ±25          | V            |
| I <sub>D</sub>   | Drain Current-continuous@ T <sub>C</sub> =25℃ | 14           | А            |
| I <sub>DM</sub>  | Pulse Drain Current                           | 56           | А            |
| P <sub>tot</sub> | Total Dissipation@T <sub>C</sub> =25℃         | 30           | W            |
| Tj               | Max. Operating Junction Temperature           | 150          | $^{\circ}$ C |
| T <sub>stg</sub> | Storage Temperature Range                     | ange -55~150 |              |

#### THERMAL CHARACTERISTICS

| SYMBOL              | PARAMETER                            | MAX  | UNIT |
|---------------------|--------------------------------------|------|------|
| R <sub>th j-c</sub> | Thermal Resistance, Junction to Case | 4.17 | °C/W |





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#### **ELECTRICAL CHARACTERISTICS**

Tc=25℃ unless otherwise specified

| SYMBOL               | PARAMETER                       | CONDITIONS  | MIN | TYPE | MAX  | UNIT |
|----------------------|---------------------------------|---|-----|------|------|------|
| V <sub>(BR)DSS</sub> | Drain-Source Breakdown Voltage  | V <sub>GS</sub> = 0; I <sub>D</sub> = 1mA                 | 500 |      |      | V    |
| V <sub>GS(th)</sub>  | Gate Threshold Voltage          | V <sub>DS</sub> = V <sub>GS</sub> ; I <sub>D</sub> =250μA | 2   |      | 4    | V    |
| R <sub>DS(on)</sub>  | Drain-Source On-Resistance      | V <sub>GS</sub> = 10V; I <sub>D</sub> = 7A                |     |      | 250  | mΩ   |
| I <sub>GSS</sub>     | Gate-Body Leakage Current       | V <sub>GS</sub> = ±25V;V <sub>DS</sub> = 0                |     |      | ±100 | nA   |
| I <sub>DSS</sub>     | Zero Gate Voltage Drain Current | V <sub>DS</sub> = Max rating                              |     |      | 1    | μΑ   |
|                      |                                 | V <sub>DS</sub> = Max rating; T <sub>C</sub> =125℃        |     |      | 100  |      |
| V <sub>SD</sub>      | Diode Forward On-Voltage        | I <sub>S</sub> = 14A;V <sub>GS</sub> = 0                  |     |      | 1.5  | V    |

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